2811

Docket No.: 50090-339

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Takashi INBE

Serial No.: 09/960,356 : Group Art Unit: 2811

Filed: September 24, 2001 : Examiner: Gene Munson

For: SEMICONDUCTOR DEVICE FOR DETECTING NEUTRON, AND METHOD FOR THE FABRICATION

THE COMMISSIONER FOR PATENTS AND TRADEMARKS
Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

- ☐ No additional fee is required.
- ☐ Applicant is entitled to small entity status under 37 CFR 1.27
- ☐ Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	6	20	0	$18.00 =	$0.00
Independent Claims	4	3	1	$84.00 =	$84.00
		Multiple claims newly presented			$0.00
		Fee for extension of time			$110.00
					$0.00
				Total of Above Calculations	$194.00

☒ Please charge my Deposit Account No. 500417 in the amount of $194.00. An additional copy of this transmittal sheet is submitted herewith.

☒ The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL & EMERY

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Date: October 24, 2002

#8/a
10/29/02

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AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

The following amendments and remarks are submitted in response to the Office Action dated June 24, 2002.

IN THE SPECIFICATION:

Please replace the paragraph beginning at page 4, line 25, with the following rewritten paragraph:

--For the formation of the boron containing layer 4 there are known several methods. In one method, boron is simultaneously doped into a film formed by a CVD method. In another method, an interlayer insulating film is formed and then boron is doped by ion implantation. The degree of radiation-activity by neutrons depends upon the number of isotopes ^{10}B existent in the boron containing layer 4. Accordingly, even if the concentration of the isotope ^{10}B in the boron containing layer 4 is low, it may be sufficient that the boron containing layer 4 is formed to be thicker. Inversely, when the concentration of the isotope ^{10}B in the boron containing layer 4 is